

MICRO ELECTRONICS

2N718

NPN
SILICON
TRANSISTOR

DESCRIPTION

2N718 is NPN silicon planar transistor designed for medium power applications.

TO-18



CBE

ABSOLUTE MAXIMUM RATINGS

| | | |
|--|----------|---------------|
| Collector-Emitter Voltage | VCER | 40V |
| Collector-Base Voltage | VCBO | 60V |
| Emitter-Base Voltage | VEBO | 5V |
| Collector Current | IC | 500mA |
| Continuous Power Dissipation | Pd | 400mW |
| Operating & Storage Junction Temperature | Tj, Tstg | -65 to +150°C |

ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25°C)

| PARAMETER | SYMBOL | MIN | MAX | UNIT | CONDITIONS |
|--------------------------------------|-----------|-----|------|------|----------------------------|
| Collector-Emitter Breakdown Voltage | LVCER | 40 | | V | IC=100μA REB=10ohm |
| Collector-Base Breakdown Voltage | BVCBO | 60 | | V | IC=100μA IE=0 |
| Emitter-Base Breakdown Voltage | BVEBO | 5 | | V | IE=10μA IC=0 |
| Collector Cutoff Current | ICBO | | 1000 | nA | VCB=30V IE=0 |
| D.C. Current Gain | HFE* | 40 | 120 | | IC=150mA VCE=10V |
| Collector-Emitter Saturation Voltage | VCE(sat)* | | 1.5 | V | IC=150mA IB=15mA |
| Base-Emitter Saturation Voltage | VBE(sat)* | | 1.3 | V | IC=150mA IB=15mA |
| Current Gain Bandwidth Product | fT | 50 | | MHz | IC=50mA VCE=10V f=20MHz |

* Pulse test : pulse width < 300μS, duty cycle < 2%.



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